

VS-16TTS...PbF Series, VS-16TTS...-M3 Series

Vishay Semiconductors

High Voltage Phase Control Thyristor, 16 A





- 40 °C to 125 °C

TO-220AB

TJ

PRODUCT SUMMARY				
Package	TO-220AB			
Diode variation	Single SCR			
I _{T(AV)}	10 A			
V _{DRM} /V _{RRM}	800 V, 1200 V			
V_{TM}	1.4 V			
I _{GT}	60 mA			

FEATURES

 Designed and qualified according to JEDEC-JESD47



- Compliant to RoHS Directive 2002/95/EC
- Halogen-free according to IEC 61249-2-21 definition (-M3 only)





ROHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-16TTS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operating up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS					
Capacitive input filter T _A = 55 °C, T _J = 125 °C, common heatsink of 1 °C/W	13.5	17	А		

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I _{T(AV)}	Sinusoidal waveform	10	۸			
I _{RMS}		16	Α			
V _{DRM} /V _{RRM}	Range (1)	800/1200	V			
I _{TSM}		200	A			
V _T	10 A, T _J = 25 °C	1.4	V			
dV/dt		500	V/µs			
dl/dt		150	A/μs			
TJ	Range	- 40 to 125	°C			

Note

⁽¹⁾ For higher voltage up to 1600 V contact factory

VOLTAGE RATINGS							
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA				
VS-16TTS08PbF, VS-16TTS08-M3	800	800	10				
VS-16TTS12PbF, VS-16TTS12-M3	1200	1200	10				



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ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL		TEST CONDITIONS	VALUES		UNITS			
PARAMETER	STIVIBUL		TEST CONDITIONS	TYP.	MAX.	UNITS			
Maximum average on-state current	I _{T(AV)}	T _C = 98 °C, 1	80° conduction, half sine wave	1	0				
Maximum RMS on-state current	I _{RMS}			1	6	A			
Maximum peak, one-cycle,	I	10 ms sine p	ulse, rated V _{RRM} applied	1	70				
non-repetitive surge current	I _{TSM}	10 ms sine p	ulse, no voltage reapplied	20	00	1			
Maximum 12t for fusing	I ² t	10 ms sine p	ulse, rated V _{RRM} applied	14	14	- A ² s			
Maximum I ² t for fusing	1-1	10 ms sine pulse, no voltage reapplied		200		7 A ² S			
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10	ms, no voltage reapplied	2000		A²√s			
Maximum on-state voltage drop	V_{TM}	10 A, T _J = 25 °C		1.4		V			
On-state slope resistance	r _t	T _J = 125 °C		1.0	mΩ				
Threshold voltage	V _{T(TO)}	1.1		.1	V				
Maximum reverse and direct lookage current	1 /1	T _J = 25 °C	V - Betad V A/	0	.5				
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	IRM/IDM	IRM/IDM	IRM/IDM	T _J = 125 °C	V _R = Rated V _{RRM} /V _{DRM}		0	
Holding current	lн	Anode supply = 6 V, resistive load, initial I _T = 1 A 16TTS08PbF, 16TTS12PbF		-	100	mA			
Maximum latching current	ΙL	Anode supply = 6 V, resistive load		Anode supply = 6 V, resistive load 20		00			
Maximum rate of rise of off-state voltage	dV/dt			50	00	V/µs			
Maximum rate of rise of turned-on current	dl/dt			15	50	A/µs			

TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum peak gate power	P_{GM}		8.0	W		
Maximum average gate power	P _{G(AV)}		2.0	VV		
Maximum peak positive gate current	+ I _{GM}		1.5	Α		
Maximum peak negative gate voltage	- V _{GM}		10	V		
	I _{GT}	Anode supply = 6 V, resistive load, T _J = - 65 °C	90			
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T _J = 25 °C	60	mA		
		Anode supply = 6 V, resistive load, T _J = 125 °C	35			
		Anode supply = 6 V, resistive load, T _J = - 65 °C	3.0			
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0	v		
voltage to trigger		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0	V		
Maximum DC gate voltage not to trigger	V_{GD}	T = 105 °C V = Peted value	0.2			
Maximum DC gate current not to trigger	I_{GD}	T _J = 125 °C, V _{DRM} = Rated value	2.0	mA		

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9			
Typical reverse recovery time	t _{rr}	T _{.I} = 125 °C	4	μs		
Typical turn-off time	tq	1	110	1		

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THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum junction and storage temperature range		T _J , T _{Stg}		- 40 to 125	°C		
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	1.3			
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W		
Typical thermal resistance, case to heatsink		R_{thCS}	Mounting surface, smooth and greased	0.5			
Approximate weight				2	g		
Approximate weight				0.07	OZ.		
Mounting torque -	minimum			6 (5)	kgf · cm		
Mounting torque —	maximum			12 (10)	(lbf · in)		
Marking device			Coop atula TO 220AP	16TTS08			
			Case style TO-220AB	16TTS12			

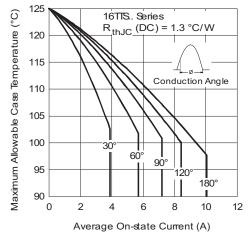


Fig. 1 - Current Rating Characteristics

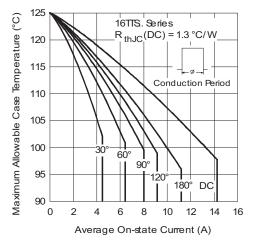


Fig. 2 - Current Rating Characteristics

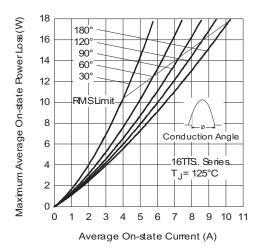


Fig. 3 - On-State Power Loss Characteristics

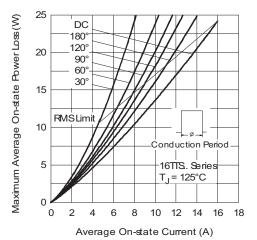


Fig. 4 - On-State Power Loss Characteristics

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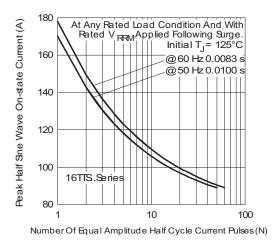


Fig. 5 - Maximum Non-Repetitive Surge Current

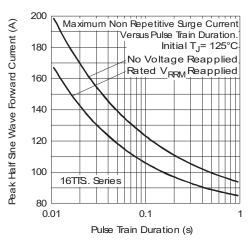


Fig. 6 - Maximum Non-Repetitive Surge Current

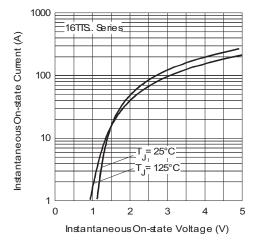


Fig. 7 - On-State Voltage Drop Characteristics

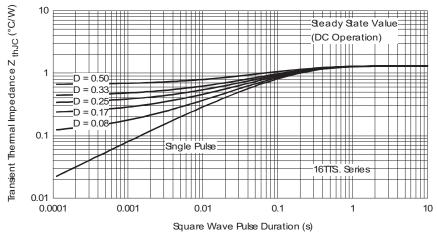


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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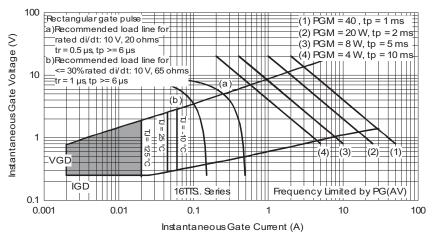
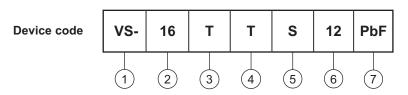


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE



1 - Vishay Semiconductors product

2 - Current rating

3 - Circuit configuration:

T = Single thyristor

4 - Package:

T = TO-220AB

5 - Type of silicon:

S = Converter grade

6 - Voltage code x 100 = V_{RRM} - 08 = 800 V 12 = 1200 V

7 | - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-16TTS08PbF	50	1000	Antistatic plastic tubes			
VS-16TTS08-M3	50	1000	Antistatic plastic tubes			
VS-16TTS12PbF	50	1000	Antistatic plastic tubes			
VS-16TTS12-M3	50	1000	Antistatic plastic tubes			

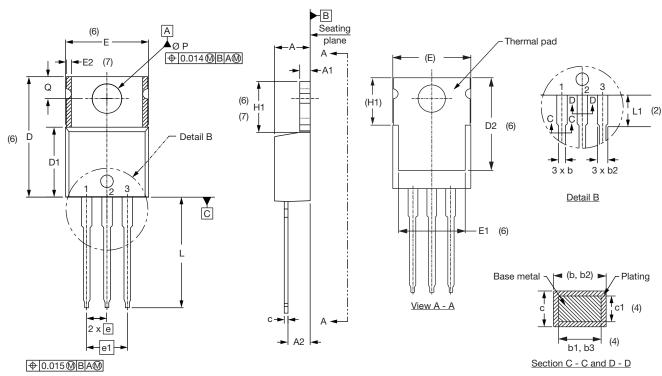
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95222</u>					
Dort moulting information	TO-220AB PbF	www.vishay.com/doc?95225			
Part marking information	TO-220AB -M3	www.vishay.com/doc?95028			



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TO-220AB

DIMENSIONS in millimeters and inches



Lead assignments

Diodes

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220AB

MILLIMETERS		IILLIMETERS INCHES		NOTES	
MIN.	MAX.	MIN.	MAX.	NOTES	
4.25	4.65	0.167	0.183		
1.14	1.40	0.045	0.055		
2.56	2.92	0.101	0.115		
0.69	1.01	0.027	0.040		
0.38	0.97	0.015	0.038	4	
1.20	1.73	0.047	0.068		
1.14	1.73	0.045	0.068	4	
0.36	0.61	0.014	0.024		
0.36	0.56	0.014	0.022	4	
14.85	15.25	0.585	0.600	3	
8.38	9.02	0.330	0.355		
11.68	12.88	0.460	0.507	6	
	MIN. 4.25 1.14 2.56 0.69 0.38 1.20 1.14 0.36 0.36 14.85 8.38	MIN. MAX. 4.25 4.65 1.14 1.40 2.56 2.92 0.69 1.01 0.38 0.97 1.20 1.73 1.14 1.73 0.36 0.61 0.36 0.56 14.85 15.25 8.38 9.02	MIN. MAX. MIN. 4.25 4.65 0.167 1.14 1.40 0.045 2.56 2.92 0.101 0.69 1.01 0.027 0.38 0.97 0.015 1.20 1.73 0.047 1.14 1.73 0.045 0.36 0.61 0.014 0.36 0.56 0.014 14.85 15.25 0.585 8.38 9.02 0.330	MIN. MAX. MIN. MAX. 4.25 4.65 0.167 0.183 1.14 1.40 0.045 0.055 2.56 2.92 0.101 0.115 0.69 1.01 0.027 0.040 0.38 0.97 0.015 0.038 1.20 1.73 0.047 0.068 1.14 1.73 0.045 0.068 0.36 0.61 0.014 0.024 0.36 0.56 0.014 0.022 14.85 15.25 0.585 0.600 8.38 9.02 0.330 0.355	

SYMBOL	MILLIN	MILLIMETERS INCHES		NOTES		
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Е	10.11	10.51	0.398	0.414	3, 6	
E1	6.86	8.89	0.270	0.350	6	
E2	-	0.76	-	0.030	7	
е	2.41	2.67	0.095	0.105		
e1	4.88	5.28	0.192	0.208		
H1	6.09	6.48	0.240	0.255	6, 7	
L	13.52	14.02	0.532	0.552		
L1	3.32	3.82	0.131	0.150	2	
ØΡ	3.54	3.73	0.139	0.147		
Q	2.60	3.00	0.102	0.118		
θ	90° to 93°		90° t	o 93°		
	•			•		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

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Lead tip



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